The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-27. (Canceled)

28. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming an amorphous semiconductor film over a substrate; and

scanning a surface of the amorphous semiconductor film with a laser light whose beam spot on the surface to be irradiated has a line shape or elliptical shape beam spot,

wherein a scanning speed of the laser light is changed depending on a position of the surface to be irradiated.

29. (Original) A method of manufacturing a semiconductor device according to claim 28, wherein the scanning speed of the laser light is determined based on an energy distribution obtained by a means for focusing the laser light.

30. (Original) A method of manufacturing a semiconductor device according to claim 28, wherein the scanning speed of the laser light is changed so that an irradiation energy on the surface to be irradiated is homogenized.

31. (Currently Amended) A method of manufacturing a semiconductor device according to claim 28, wherein the laser ~~oscillator~~ is a continuous oscillation solid laser.

32. (Currently Amended) A method of manufacturing a semiconductor device according to claim 28, wherein the laser ~~oscillator~~ is at least one selected from the group consisting of a continuous oscillation YAG laser, YVO_4 laser, YLF laser, $YAlO_3$ laser, Y_2O_3 laser, Alexandrite laser, and Ti: Sapphire laser.

33. (Currently Amended) A method of manufacturing a semiconductor device according to claim 28, wherein the laser ~~oscillator~~ is one of a continuous oscillation Ar laser or Kr laser.

34. (Original) A method of manufacturing a semiconductor device according to claim 28, wherein the laser light is a harmonic wave.

35. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming an amorphous semiconductor film over a substrate; and

scanning a surface of the amorphous semiconductor film with a laser light whose beam spot on the surface to be irradiated has a line shape or an elliptical shape beam spot,

wherein the shape of the beam spot is kept constant during the scanning, and

wherein [[the]] a scanning speed of the laser light is changed depending on a position of the surface to be irradiated.

36. (Original) A method of manufacturing a semiconductor device according to claim 35, wherein the shape of the laser light is kept constant by adjusting a focal point of the laser light on the surface to be irradiated.

37. (Original) A method of manufacturing a semiconductor device according to claim 35, wherein the scanning speed of the laser light is determined based on an energy distribution obtained by a means for focusing the laser light.

38. (Original) A method of manufacturing a semiconductor device according to claim 35, wherein the scanning speed of the laser light is changed so that an irradiation energy on the surface to be irradiated is homogenized.

39. (Currently Amended) A method of manufacturing a semiconductor device according to claim 35, wherein the laser ~~oscillator~~ is a continuous oscillation solid laser.

40. (Currently Amended) A method of manufacturing a semiconductor device according to claim 35, wherein the laser ~~oscillator~~ is at least one selected from the group consisting of a continuous oscillation YAG laser, YVO_4 laser, YLF laser, $YAlO_3$ laser, Y_2O_3 laser, Alexandrite laser, and Ti: Sapphire laser.

41. (Currently Amended) A method of manufacturing a semiconductor device according to claim 35, wherein the laser ~~oscillator~~ is one of a continuous oscillation Ar laser or Kr laser.

42. (Original) A method of manufacturing a semiconductor device according to claim 35, wherein the laser light is a harmonic wave.

43. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming an amorphous semiconductor film over a substrate;

converting a laser light emitted from a laser oscillator so that a beam spot on a surface of the amorphous semiconductor film becomes a line shape or an elliptical shape beam spot; and

deflecting a converted laser light and scanning the laser light while keeping the shape of laser light constant on the surface to be irradiated,

wherein a scanning speed of the laser light is changed depending on a position of the surface to be irradiated by controlling an operating speed of the deflecting means.

44. (Original) A method of manufacturing a semiconductor device according to claim 43, wherein the means for deflecting the converted laser light and the means for scanning while keeping the deflected laser light constant has at least one of a galvanometer mirror, a polygon mirror, an fθ lens, and a telecentric fθ lens.

45. (Original) A method of manufacturing a semiconductor device according to claim 43, wherein the shape of the laser light is kept constant by adjusting a focal point of the laser light on the surface to be irradiated.

46. (Original) A method of manufacturing a semiconductor device according to claim 43, wherein the scanning speed of the laser light is determined based on an energy distribution obtained by a means for focusing the laser light.

47. (Original) A method of manufacturing a semiconductor device according to claim 43, wherein the scanning speed of the laser light is changed so that an irradiation energy on the surface to be irradiated is homogenized.

48. (Original) A method of manufacturing a semiconductor device according to claim 43, wherein the laser oscillator is a continuous oscillation solid laser.

49. (Original) A method of manufacturing a semiconductor device according to claim 43, wherein the laser oscillator is at least one selected from the group consisting of a continuous oscillation YAG laser, YVO_4 laser, YLF laser, $YAlO_3$ laser, Y_2O_3 laser, Alexandrite laser, and Ti: Sapphire laser.

50. (Original) A method of manufacturing a semiconductor device according to claim 43, wherein the laser oscillator is one of a continuous oscillation Ar laser or Kr laser.

51. (Original) A method of manufacturing a semiconductor device according to claim 43, wherein the laser light is a harmonic wave.

52. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming an amorphous semiconductor film over a substrate; and

scanning a surface of the amorphous semiconductor film with a laser light,

wherein a scanning speed of the laser light is changed depending on a position of the surface.

53. (Previously Presented) A method of manufacturing a semiconductor device according to claim 52, wherein the scanning speed of the laser light is determined based on an energy distribution obtained by a means for focusing the laser light.

54. (Previously Presented) A method of manufacturing a semiconductor device according to claim 52, wherein the scanning speed of the laser light is changed so that an irradiation energy on the surface to be irradiated is homogenized.

55. (Currently Amended) A method of manufacturing a semiconductor device according to claim 52, wherein the laser ~~oscillator~~ is a continuous oscillation solid laser.

56. (Currently Amended) A method of manufacturing a semiconductor device according to claim 52, wherein the laser ~~oscillator~~ is at least one selected from the group consisting of a continuous oscillation YAG laser, YVO_4 laser, YLF laser, $YAlO_3$ laser, Y_2O_3 laser, Alexandrite laser, and Ti: Sapphire laser.

57. (Currently Amended) A method of manufacturing a semiconductor device according to claim 52, wherein the laser ~~oscillator~~ is one of a continuous oscillation Ar laser or Kr laser.

58. (Previously Presented) A method of manufacturing a semiconductor device according to claim 52, wherein the laser light is a harmonic wave.

59. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming an amorphous semiconductor film over a substrate; and

scanning a surface of the amorphous semiconductor film with a laser light,

wherein a shape of the beam spot is kept constant during the scanning, and

wherein [[the]] a scanning speed of the laser light is changed depending on a position of the surface.

60. (Previously Presented) A method of manufacturing a semiconductor device according to claim 59, wherein the shape of the laser light is kept constant by adjusting a focal point of the laser light on the surface to be irradiated.

61. (Previously Presented) A method of manufacturing a semiconductor device according to claim 59, wherein the scanning speed of the laser light is determined based on an energy distribution obtained by a means for focusing the laser light.

62. (Previously Presented) A method of manufacturing a semiconductor device according to claim 59, wherein the scanning speed of the laser light is changed so that an irradiation energy on the surface to be irradiated is homogenized.

63. (Currently Amended) A method of manufacturing a semiconductor device according to claim 59, wherein the laser ~~oscillator~~ is a continuous oscillation solid laser.

64. (Currently Amended) A method of manufacturing a semiconductor device according to claim 59, wherein the laser ~~oscillator~~ is at least one selected from the group consisting of a continuous oscillation YAG laser, YVO_4 laser, YLF laser, $YAlO_3$ laser, Y_2O_3 laser, Alexandrite laser, and Ti: Sapphire laser.

65. (Currently Amended) A method of manufacturing a semiconductor device according to claim 59, wherein the laser ~~oscillator~~ is one of a continuous oscillation Ar laser or Kr laser.

66. (Previously Presented) A method of manufacturing a semiconductor device according to claim 59, wherein the laser light is a harmonic wave.

67. (New) A method of manufacturing a semiconductor device according to claim 28, wherein the scanning speed becomes higher as the irradiation position gets closer to a center of the substrate.

68. (New) A method of manufacturing a semiconductor device according to claim 35, wherein the scanning speed becomes higher as the irradiation position gets closer to a center of the substrate.

69. (New) A method of manufacturing a semiconductor device according to claim 43, wherein the scanning speed becomes higher as the irradiation position gets closer to a center of the substrate.

70. (New) A method of manufacturing a semiconductor device according to claim 52, wherein the scanning speed becomes higher as the irradiation position gets closer to a center of the substrate.

71. (New) A method of manufacturing a semiconductor device according to claim 59, wherein the scanning speed becomes higher as the irradiation position gets closer to a center of the substrate.